TSA40N20M

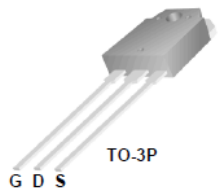
200V N-Channel MOSFET

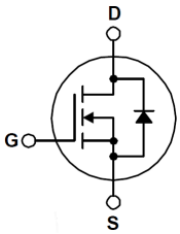
General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 40A,200V,Max.RDS(on)=65mΩ @ VGS=10V
- Low gate charge:Qg=62nC (Typ.)
- Low reverse transfer capacitance: Crss=50pF (Typ.)
- Lower EMI noise
- 100% avalanche tested
- RoHS compliant device





Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter		TSA40N20M	Units
V_{DSS}	Drain-Source Voltage		200	V
V_{GS}	Gate-Source Voltage		± 30	V
I_D	Drain Current	T_C = 25℃	40	A
		T_C = 100℃	25.3	A
I_{DM}	Pulsed Drain Current	(Note 1)	160	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1066	mJ
I_{AR}	Repetitive avalanche current	(Note 1)	40	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	5.8	mJ
P_D	Power Dissipation		260	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

* Drain current limited by maximum junction temperature.

Thermal Resistance Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case	Max.0.48	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient	Max.62.5	℃/W

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Electrical Characteristics T_C=25℃ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 20A	--	50	65	mΩ
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	200	--	--	V
△BVDSS / △TJ	Breakdown Voltage Temperature Coefficient	ID = 250 uA, Referenced to 25℃	--	1	--	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200 V, V_{GS} = 0 V	--	--	10	uA
		V_{DS} = 200 V, T_J = 125℃	--	--	100	uA
I_{GSSF}	Gate-Body Leakage Current,Forward	V_{GS} = 20 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current,Reverse	V_{GS} =- 20 V, V_{DS} = 0 V	--	--	-100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	2684	--	pF
C_{oss}	Output Capacitance		--	382	--	pF
C_{rss}	Reverse Transfer Capacitance		--	50	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 100V, I_D = 20A, R_G = 25 Ω (Note 3,4)	--	40	--	ns
t_r	Turn-On Rise Time		--	25	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	157	--	ns
t_f	Turn-Off Fall Time		--	35	--	ns
Q_g	Total Gate Charge	V_{DS} = 100 V, I_D = 20A, V_{GS} = 10 V (Note 3,4)	--	62	--	nC
Q_{gs}	Gate-Source Charge		--	16	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	40	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	160	A
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 40A, V_{GS} = 0 V	--	--	1.4	V
t_{rr}	Reverse Recovery Time	I_S =20A, V_{GS} = 0 V di_F/dt = 100 A/μs (Note 3,4)	--	185	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.2	--	uC

NOTES:

1. Repetitive Rating: Pulse width limited by safe operating area
2. L=1mH, I_{AS}=40A, V_{DD}=50V, R_G=25 Ω,Starting TJ=25 ℃
3. Pulse test: Pulse width≤300us, Duty cycle≤2%
4. Essentially independent of operating temperature typical characteristics

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Typical Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

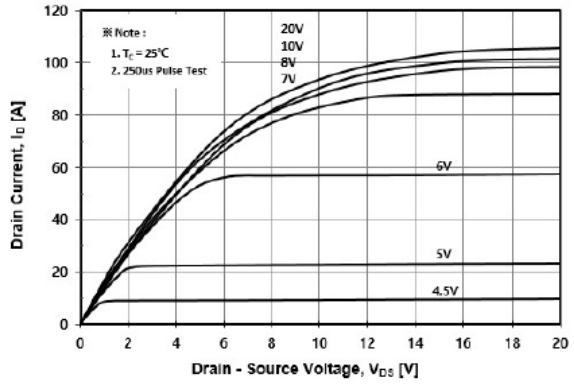


Fig. 2 Typical Transfer Characteristics

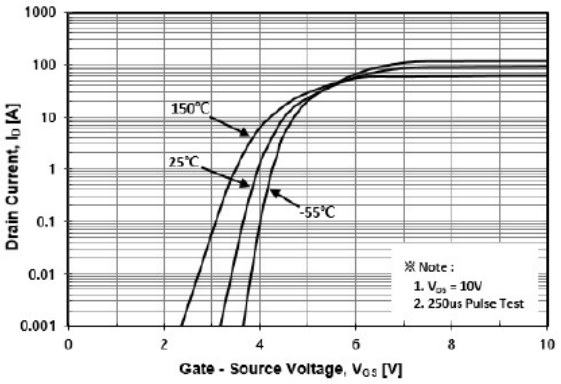


Fig.3 On-Resistance Variation with Drain Current and Gate Voltage

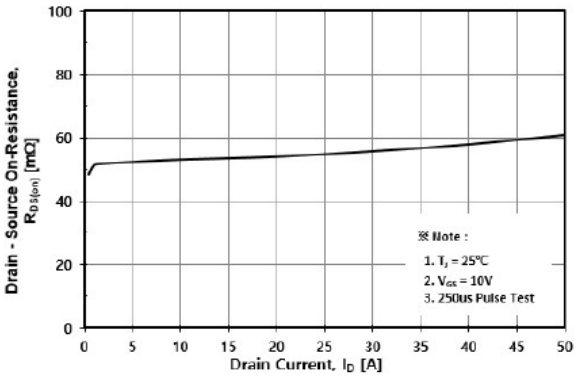


Fig. 4 Body Diode Forward Voltage Variation with Source Current

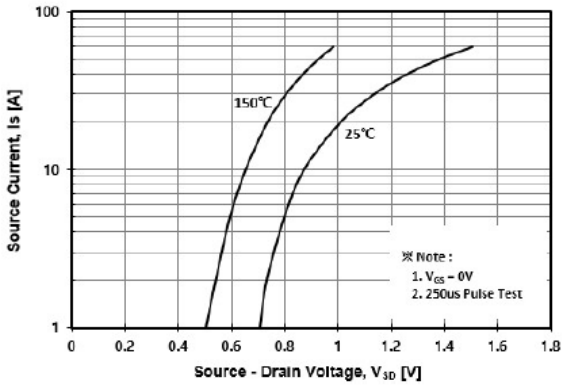


Fig. 5 Typical Capacitance Characteristics

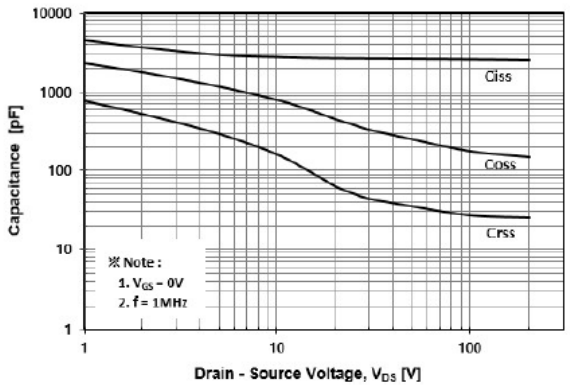
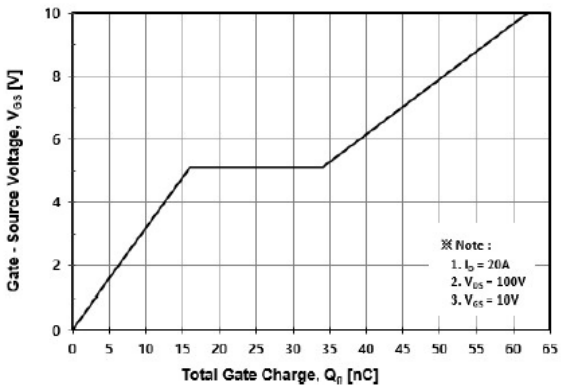


Fig. 6 Typical Total Gate Charge Characteristics



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Typical Electrical Characteristics Curves

Fig. 7 Breakdown Voltage Variation vs. Temperature

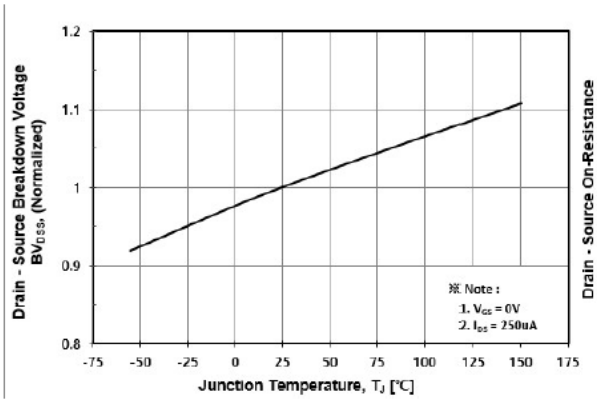

Fig. 8 On-Resistance Variation vs. Temperature

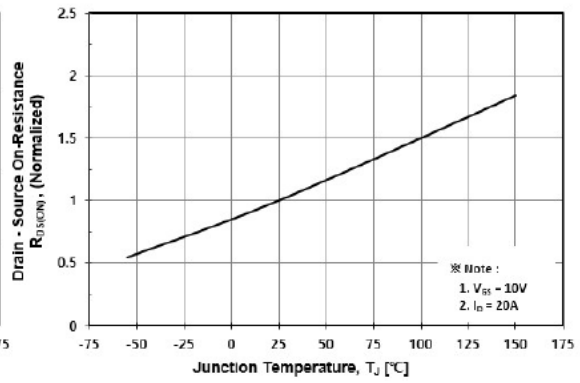

Fig. 9 Maximum Drain Current vs. Case Temperature

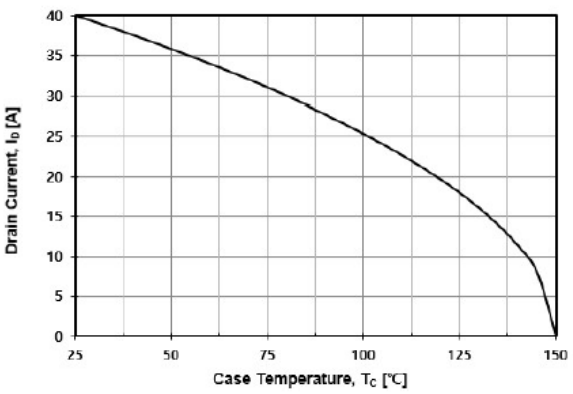

Fig. 10 Maximum Safe Operating Area

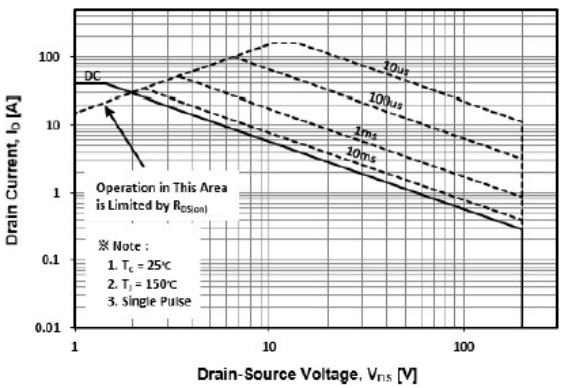

Fig. 11 Transient Thermal Impedance

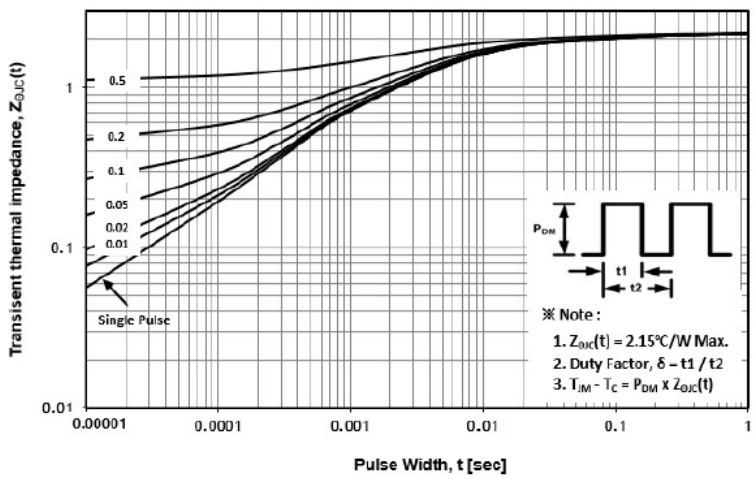

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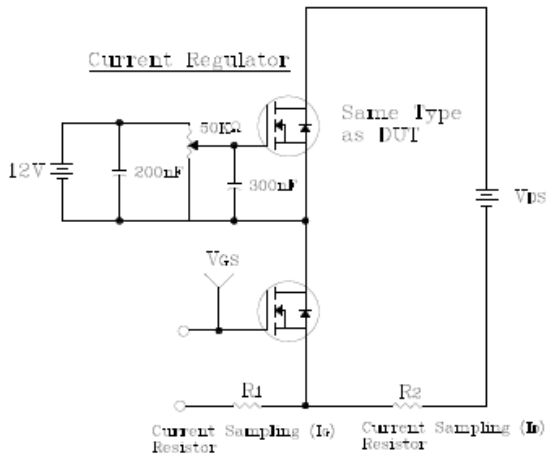
Fig. 12 Gate Charge Test Circuit & Waveform



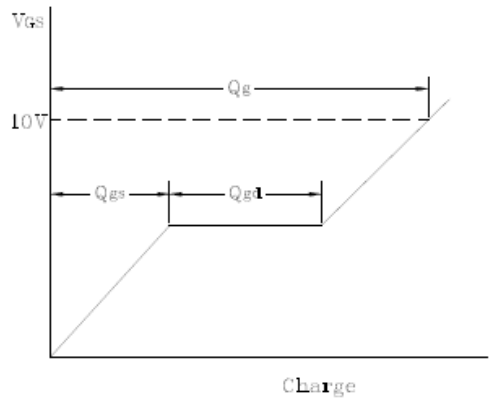
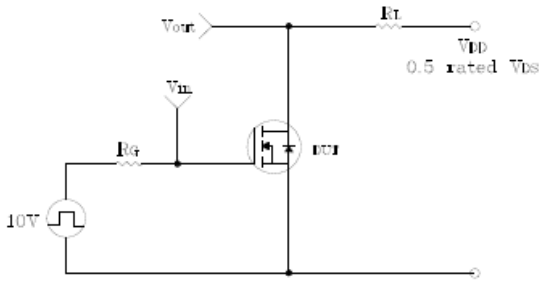


Fig. 13 Resistive Switching Test Circuit & Waveform



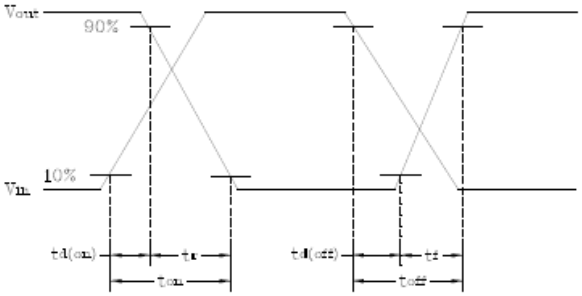
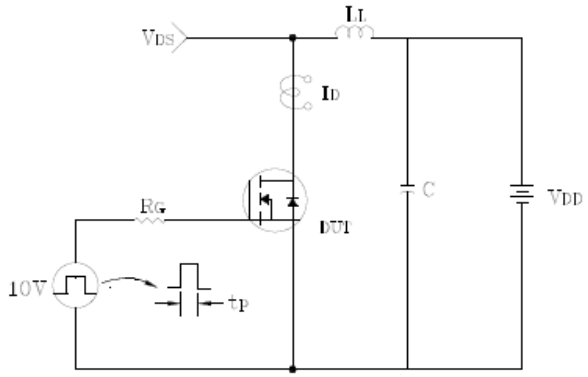


Fig. 14 EAS Test Circuit & Waveform



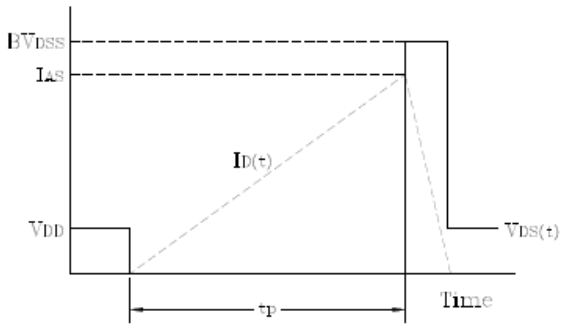


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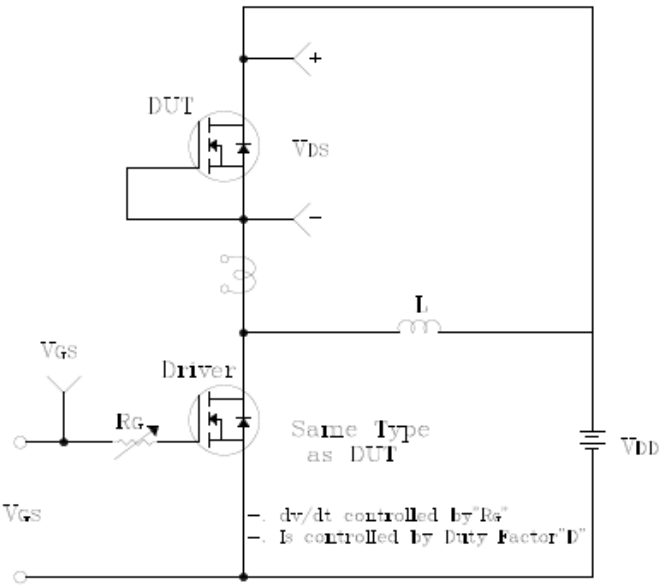
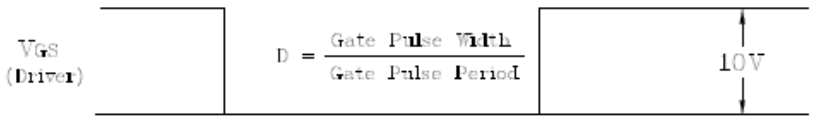
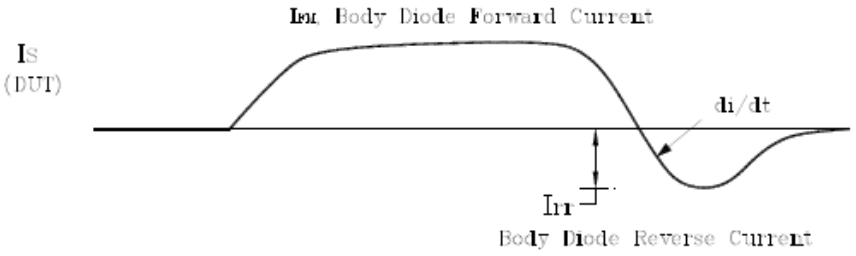
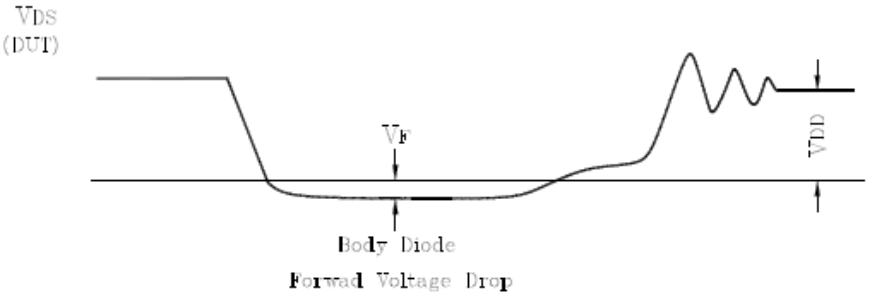
Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform









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